NSN 5961-01-131-5786

Photo Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-131-5786 **Inclosure Material:** Plastic **Overall Length:** Between 0.140 inches and 0.210 inches **Terminal Length:** 0.400 inches **Overall Diameter:** Between 0.190 inches and 0.210 inches **Function For Which Designed:** Phototransistor **Mounting Method: Terminal Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 80.0 collector to base voltage/static/emitter open and 30.0 collector to emitter voltage/static/base open and 5.0 emitter to base voltage, static, collector open **Current Rating Per Characteristic:** 25.00 milliamperes source cutoff current **Power Rating Per Characteristic:** 200.0 milliwatts small-signal input power, common-collector preset **Maximum Operating Tempurature Per Measurement Point:** 85.0 degrees celsius junction **Terminal Type And Quantity:** 3 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** Yes - demil/mli Fiig: A110a0